

2023 5th International Conference on Radiation Effects of Electronic Devices (ICREED 2023)

**Kunming, China
24-27 May 2023**



**IEEE Catalog Number: CFP23K44-POD
ISBN: 979-8-3503-5888-9**

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|-------------------------|-------------------|
| IEEE Catalog Number: | CFP23K44-POD |
| ISBN (Print-On-Demand): | 979-8-3503-5888-9 |
| ISBN (Online): | 979-8-3503-5887-2 |

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